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JAPANESE PATENT OFFICE

PATENT ABSTRACTS OF JAPAN

(11) Publication number: 2002246514 A

(43) Date of publication of application: 30.08.02

(51) Int. Cl
H01L 23/34
H01L 21/3065
H01L 27/04
H01L 21/822

(21) Application number: 2001036351

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(22) Date of filing: 14.02.01

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(54) SEMICONDUCTOR DEVICE

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(57) Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor device having an improved heat radiation efficiency on a rear face.

SOLUTION: An active region 2 is formed in a surface layer of a first principal plane 101 of a semiconductor substrate 100, and trenches 3 are formed in a rear face 102 which is a second principal plane, to turn the rear face 102 uneven (concave where trenches are formed and convex where trenches are not formed). On the uneven rear face 102, a heat radiation thin film 7 formed of such a material as to have a larger coefficient of thermal conductivity than the semiconductor substrate 100 (i.e., a thin film for heat radiation) is formed along the uneven surface. A ratio of the depth L to the width W of the trenches 3, that is, an aspect ratio (L/W) is set to 1 or above and 50 or below. The width of the trenches 3 and a distance D between the trenches 3 are set between 1 μm and 100 μm .

